2023년 2월 15일(수), 09:00-10:30
Room E (루비 II, 5층)

E. Compound Semiconductors 분과
[WE1-E] Compound Semiconductor I

좌장: 임유승 교수(세종대학교)

WE1-E-1 **09:00-09:15**	**Record In$_{0.8}$Ga$_{0.2}$As Quantum-well HEMTs for 6G Applications** Wan-Soo Park[1], Hyeon-Bhin Jo[1], Hyo-Jin Kim[1], Su-Min Choi[1], Ji-Hoon Yoo[1], Hyeon-Seok Jeong[1], Takuya Tsutsumi[2], Hiroki Sugiyama[2], Hideaki Matsuzaki[2], Jae-Hak Lee[1], and Dae-Hyun Kim[1] *[1]School of Electronic and Electrical Engineering, Kyungpook National University, [2]NTT Device Technology Laboratories*
WE1-E-2 **09:15-09:30**	**High-speed and Low-voltage Operating Charge Trap Device based on InGaAs TFETs for Low-power Neuromorphic Application** Dae-Hwan Ahn[1], Suman Hu[1,2], Kyeol Ko[1], Donghee Park[1], Hoyung Suh[1], Gyu-Tae Kim[2], Jae-Hoon Han[1], Jin-Dong Song[1], and Yeon Joo Jeong[1] *[1]KIST, [2]Korea University*
WE1-E-3 **09:30-09:45**	**Explicit Thermal Resistance Model of Self-heating Effects of AlGaN/GaN HEMTs with Linear and Non-linear Thermal Conductivity** Surajit Chakraborty[1], Walid Amir[1], Ju-Won Shin[1], Ki-Yong Shin[1], Takuya Hoshi[2], Takuya Tsutsumi[2], Hiroki Sugiyama[2], Hideaki Matsuzaki[2], and Tae-Woo Kim[1] *[1]Department of Electrical, Electronic and Computer Engineering, University of Ulsan, [2]NTT Device Technology Laboratories, NTT Corporation*
WE1-E-4 **09:45-10:00**	**Investigation for Spatial Distribution of Oxide Trap Density by Low-Frequency Noise Characterization in β-Ga$_2$O$_3$ FinFET** Jae Wook Yoo[1], Hong Seung Lee[1], Hyeon Jun Song[1], Seongbin Lim[1], Jungsik Kim[4], Kihyun Kim[1], Jun-Young Park[3], Yang-Kyu Choi[2], and Hagyoul Bae[1] *[1]Jeonbuk National University, [2]KAIST, [3]Chungbuk National University, [4]Gyeongsang National University*
WE1-E-5 **10:00-10:15**	**Full Stepper-Based InP Double-Heterojunction Bipolar Transistors (DHBTs) with f_T & $f_{max} \geq 250$ GHz** Hyeon-Seok Jeong[1,2], Yong-Hyun Kim[1], Jacob Yun[1], Ji-Min Beak[2], Ji-Hoon Yoo[2], Su-Min Choi[2], Wan-Soo Park[2], Hyo-Jin Kim[2], In-Geun Lee[2], Ted Kim[1], Jae-Hak Lee[2], Hyuk-Min Kwon[3], Seung Heon Shin[3], and Dae-Hyun Kim[2] *[1]QSI Inc., [2]Kyungpook National University, [3]Korea Polytechnics*
WE1-E-6 **10:15-10:30**	**5-levels-stacked In$_{0.53}$Ga$_{0.47}$As MBCFETs with Regrown S/D Contacts** In-Geun Lee[1], Hyeon-Bhin Jo[1], Ji-Hoon Yoo[1], Hyunchul Jang[2], Minwoo Kong[2], Hyeon-Seok Jeong[1], Wan-Soo Park[1], Sang-Kuk Kim[3], Jae-Gyu Kim[3], Jacob Yun[3], Ted Kim[3], Jae-Hak Lee[1], Chan-Soo Shin[2], Kwang-Seok Seo[2], and Dae-Hyun Kim[1] *[1]Kyungpook National University, [2]KANC, [3]QSI Inc.*